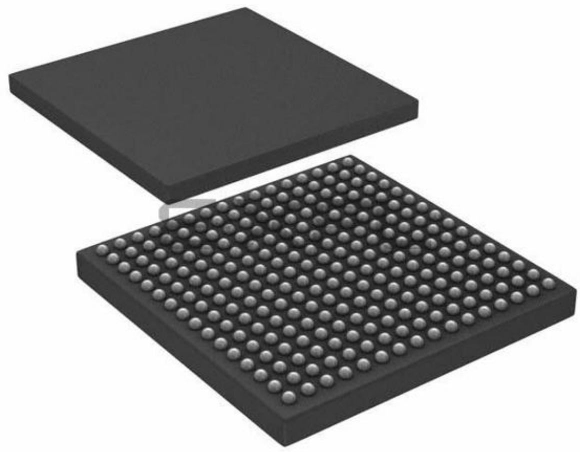

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	36864
Number of I/O	114
Number of Gates	250000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1afs250-2fg256

Clocking Resources

The Fusion family has a robust collection of clocking peripherals, as shown in the block diagram in Figure 2-16. These on-chip resources enable the creation, manipulation, and distribution of many clock signals. The Fusion integrated RC oscillator produces a 100 MHz clock source with no external components. For systems requiring more precise clock signals, the Fusion family supports an on-chip crystal oscillator circuit. The integrated PLLs in each Fusion device can use the RC oscillator, crystal oscillator, or another on-chip clock signal as a source. These PLLs offer a variety of capabilities to modify the clock source (multiply, divide, synchronize, advance, or delay). Utilizing the CCC found in the popular ProASIC3 family, Fusion incorporates six CCC blocks. The CCCs allow access to Fusion global and local clock distribution nets, as described in the "Global Resources (VersaNets)" section on page 2-11.

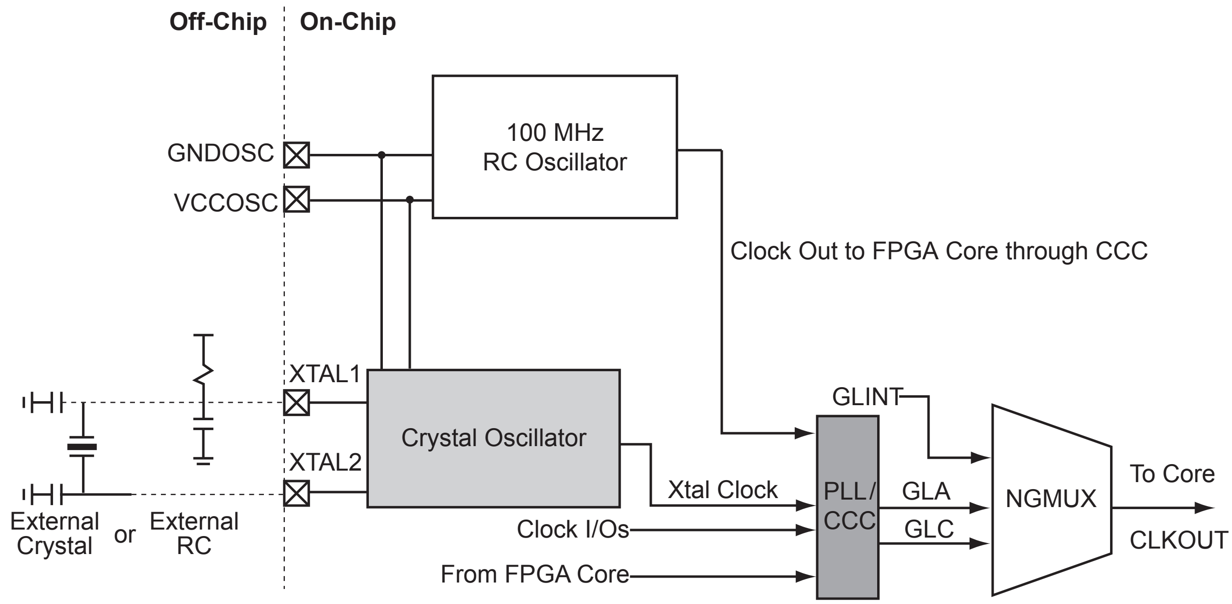

Figure 2-16 **• Fusion Clocking Options**

***Table 2-50* • ADC Characteristics in Direct Input Mode**
Commercial Temperature Range Conditions, T_J = 85°C (unless noted otherwise),
Typical: VCC33A = 3.3 V, VCC = 1.5 V

Parameter	Description	Condition	Min.	Typ.	Max.	Units
Direct Input using Analog Pad AV, AC, AT						
VINADC	Input Voltage (Direct Input)	Refer to Table 3-2 on page 3-3				
CINADC	Input Capacitance	Channel not selected		7		pF
		Channel selected but not sampling		8		pF
		Channel selected and sampling		18		pF
ZINADC	Input Impedance	8-bit mode		2		kΩ
		10-bit mode		2		kΩ
		12-bit mode		2		kΩ
Analog Reference Voltage VAREF						
VAREF	Accuracy	T_J = 25°C	2.537	2.56	2.583	V
	Temperature Drift of Internal Reference			65		ppm / °C
	External Reference		2.527		VCC33A + 0.05	V
ADC Accuracy (using external reference) [1,2]						
DC Accuracy						
TUE	Total Unadjusted Error	8-bit mode		0.29		LSB
		10-bit mode		0.72		LSB
		12-bit mode		1.8		LSB
INL	Integral Non-Linearity	8-bit mode		0.20	0.25	LSB
		10-bit mode		0.32	0.43	LSB
		12-bit mode		1.71	1.80	LSB
DNL	Differential Non-Linearity (no missing code)	8-bit mode		0.20	0.24	LSB
		10-bit mode		0.60	0.65	LSB
		12-bit mode		2.40	2.48	LSB
	Offset Error	8-bit mode		0.01	0.17	LSB
		10-bit mode		0.05	0.20	LSB
		12-bit mode		0.20	0.40	LSB
	Gain Error	8-bit mode		0.0004	0.003	LSB
		10-bit mode		0.002	0.011	LSB
		12-bit mode		0.007	0.044	LSB
	Gain Error (with internal reference)	All modes		2		% FSR

Notes:

1. *Accuracy of the external reference is 2.56 V ± 4.6 mV.*
2. *Data is based on characterization.*
3. *The sample rate is time-shared among active analog inputs.*

Solution 3

The board-level design must ensure that the reflected waveform at the pad does not exceed limits provided in Table 3-4 on page 3-4. This is a long-term reliability requirement.

This scheme will also work for a 3.3 V PCI/PCIX configuration, but the internal diode should not be used for clamping, and the voltage must be limited by the bus switch, as shown in Figure 2-105. Relying on the diode clamping would create an excessive pad DC voltage of 3.3 V + 0.7 V = 4 V.

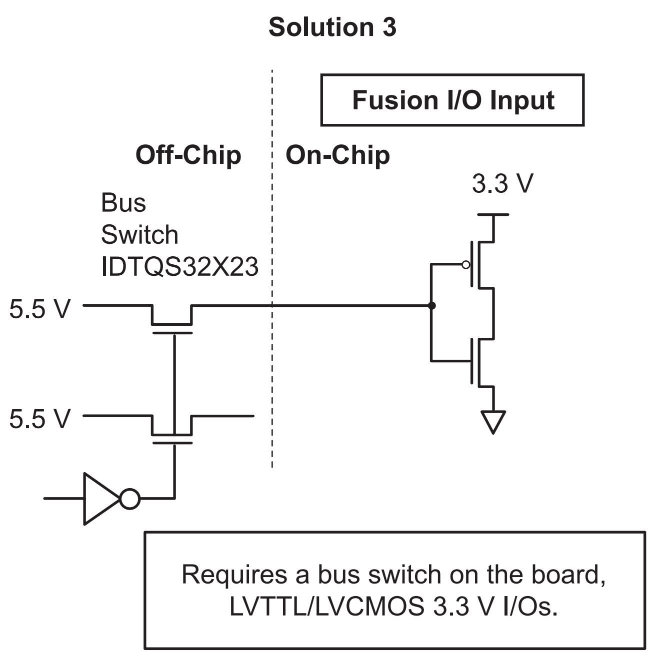

Figure 2-105 **• Solution 3**

Solution 4

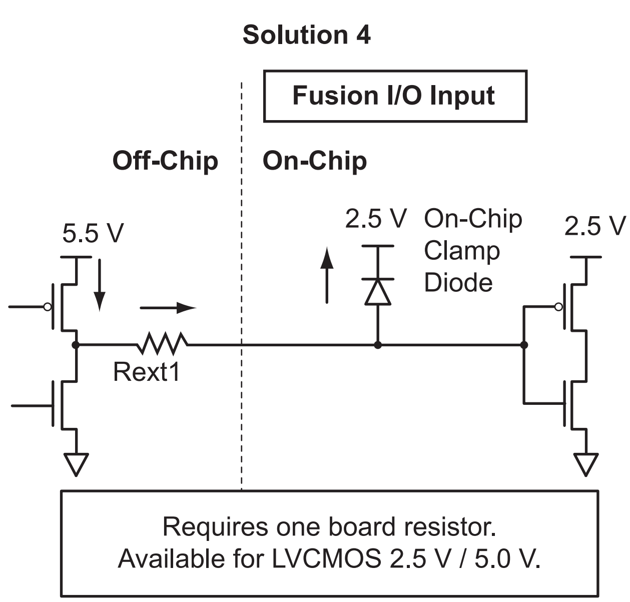

Figure 2-106 **• Solution 4**

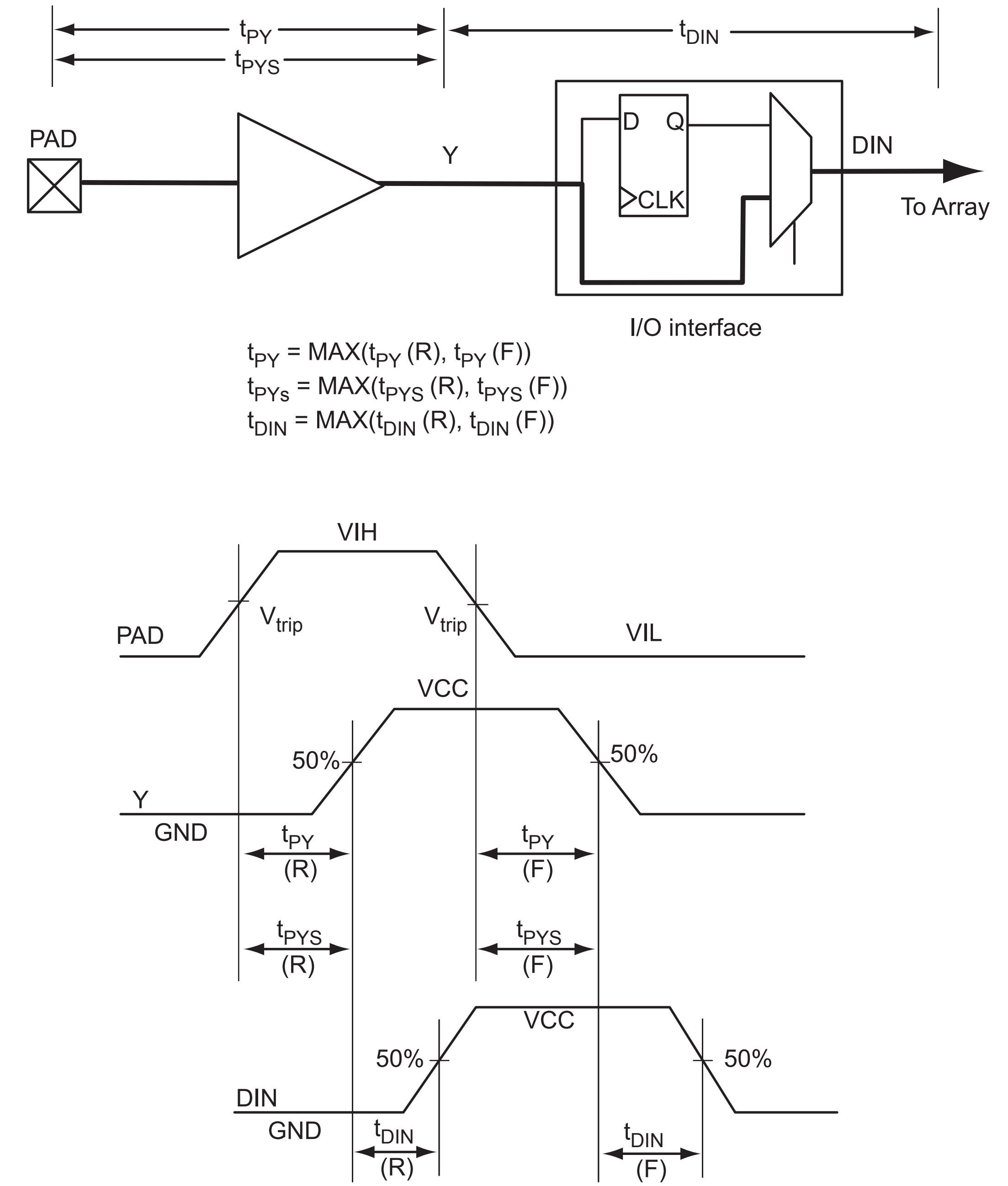

***Figure 2-116* • Input Buffer Timing Model and Delays (example)**

Table 2-109 **• 3.3 V LVTTL / 3.3 V LVCMOS High Slew**
Commercial Temperature Range Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = 3.0 V
Applicable to Standard I/Os

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.66	7.07	0.04	1.00	0.43	7.20	6.23	2.07	2.15	ns
	–1	0.56	6.01	0.04	0.85	0.36	6.12	5.30	1.76	1.83	ns
	–2 [2]	0.49	5.28	0.03	0.75	0.32	5.37	4.65	1.55	1.60	ns
4 mA	Std.	0.66	7.07	0.04	1.00	0.43	7.20	6.23	2.07	2.15	ns
	–1	0.56	6.01	0.04	0.85	0.36	6.12	5.30	1.76	1.83	ns
	–2	0.49	5.28	0.03	0.75	0.32	5.37	4.65	1.55	1.60	ns
6 mA	Std.	0.66	4.41	0.04	1.00	0.43	4.49	3.75	2.39	2.69	ns
	–1	0.56	3.75	0.04	0.85	0.36	3.82	3.19	2.04	2.29	ns
	–2	0.49	3.29	0.03	0.75	0.32	3.36	2.80	1.79	2.01	ns
8 mA	Std.	0.66	4.41	0.04	1.00	0.43	4.49	3.75	2.39	2.69	ns
	–1	0.56	3.75	0.04	0.85	0.36	3.82	3.19	2.04	2.29	ns
	–2	0.49	3.29	0.03	0.75	0.32	3.36	2.80	1.79	2.01	ns

Note: For the derating values at specific junction temperature and voltage supply levels, refer to Table 3-7 on page 3-9.

***Table 2-125* • 1.8 V LVCMOS High Slew**
Commercial Temperature Range Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V
Applicable to Standard I/Os

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.66	11.21	0.04	1.20	0.43	8.53	11.21	1.99	1.21	ns
	–1	0.56	9.54	0.04	1.02	0.36	7.26	9.54	1.69	1.03	ns
	–2	0.49	8.37	0.03	0.90	0.32	6.37	8.37	1.49	0.90	ns
4 mA	Std.	0.66	6.34	0.04	1.20	0.43	5.38	6.34	2.41	2.48	ns
	–1	0.56	5.40	0.04	1.02	0.36	4.58	5.40	2.05	2.11	ns
	–2	0.49	4.74	0.03	0.90	0.32	4.02	4.74	1.80	1.85	ns

Note: For the derating values at specific junction temperature and voltage supply levels, refer to *Table 3-7 on page 3-9.*

ATRTN*x* **Temperature Monitor Return**

AT returns are the returns for the temperature sensors. The cathode terminal of the external diodes should be connected to these pins. There is one analog return pin for every two Analog Quads. The *x* in the ATRTN*x* designator indicates the quad pairing (*x* = 0 for AQ1 and AQ2, *x* = 1 for AQ2 and AQ3, ..., *x* = 4 for AQ8 and AQ9). The signals that drive these pins are called out as ATRETURN*xy* in the software (where *x* and *y* refer to the quads that share the return signal). ATRTN is internally connected to ground. It can be left floating when it is unused. The maximum capacitance allowed across the AT pins is 500 pF.

GL **Globals**

GL I/Os have access to certain clock conditioning circuitry (and the PLL) and/or have direct access to the global network (spines). Additionally, the global I/Os can be used as Pro I/Os since they have identical capabilities. Unused GL pins are configured as inputs with pull-up resistors. See more detailed descriptions of global I/O connectivity in the "Clock Conditioning Circuits" section on page 2-22.

Refer to the "User I/O Naming Convention" section on page 2-158 for a description of naming of global pins.

JTAG Pins

Fusion devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). VCC must also be powered for the JTAG state machine to operate, even if the device is in bypass mode; VJTAG alone is insufficient. Both VJTAG and VCC to the Fusion part must be supplied to allow JTAG signals to transition the Fusion device.

Isolating the JTAG power supply in a separate I/O bank gives greater flexibility with supply selection and simplifies power supply and PCB design. If the JTAG interface is neither used nor planned to be used, the VJTAG pin together with the TRST pin could be tied to GND.

TCK **Test Clock**

Test clock input for JTAG boundary scan, ISP, and UJTAG. The TCK pin does not have an internal pull-up/-down resistor. If JTAG is not used, Microsemi recommends tying off TCK to GND or VJTAG through a resistor placed close to the FPGA pin. This prevents JTAG operation in case TMS enters an undesired state.

Note that to operate at all VJTAG voltages, 500 Ω to 1 kΩ will satisfy the requirements. Refer to Table 2-183 for more information.

Table 2-183 **• Recommended Tie-Off Values for the TCK and TRST Pins**

VJTAG	Tie-Off Resistance[2, 3]
VJTAG at 3.3 V	200 Ω to 1 kΩ
VJTAG at 2.5 V	200 Ω to 1 kΩ
VJTAG at 1.8 V	500 Ω to 1 kΩ
VJTAG at 1.5 V	500 Ω to 1 kΩ

Notes:

1. *Equivalent parallel resistance if more than one device is on JTAG chain.*
2. *The TCK pin can be pulled up/down.*
3. *The TRST pin can only be pulled down.*

TDI **Test Data Input**

Serial input for JTAG boundary scan, ISP, and UJTAG usage. There is an internal weak pull-up resistor on the TDI pin.

TDO **Test Data Output**

Serial output for JTAG boundary scan, ISP, and UJTAG usage.

XTAL2 **Crystal Oscillator Circuit Input**

Input to crystal oscillator circuit. Pin for connecting external crystal, ceramic resonator, RC network, or external clock input. When using an external crystal or ceramic oscillator, external capacitors are also recommended (Please refer to the crystal oscillator manufacturer for proper capacitor value).

If using external RC network or clock input, XTAL1 should be used and XTAL2 left unconnected. In the case where the Crystal Oscillator block is not used, the XTAL1 pin should be connected to GND and the XTAL2 pin should be left floating.

Security

Fusion devices have a built-in 128-bit AES decryption core. The decryption core facilitates highly secure, in-system programming of the FPGA core array fabric and the FlashROM. The FlashROM and the FPGA core fabric can be programmed independently from each other, allowing the FlashROM to be updated without the need for change to the FPGA core fabric. The AES master key is stored in on-chip nonvolatile memory (flash). The AES master key can be preloaded into parts in a security-protected programming environment (such as the Microsemi in-house programming center), and then "blank" parts can be shipped to an untrusted programming or manufacturing center for final personalization with an AES-encrypted bitstream. Late stage product changes or personalization can be implemented easily and with high level security by simply sending a STAPL file with AES-encrypted data. Highly secure remote field updates over public networks (such as the Internet) are possible by sending and programming a STAPL file with AES-encrypted data. For more information, refer to the *Fusion Security* application note.

128-Bit AES Decryption

The 128-bit AES standard (FIPS-197) block cipher is the National Institute of Standards and Technology (NIST) replacement for DES (Data Encryption Standard FIPS46-2). AES has been designed to protect sensitive government information well into the 21st century. It replaces the aging DES, which NIST adopted in 1977 as a Federal Information Processing Standard used by federal agencies to protect sensitive, unclassified information. The 128-bit AES standard has 3.4×10^{38} possible 128-bit key variants, and it has been estimated that it would take 1,000 trillion years to crack 128-bit AES cipher text using exhaustive techniques. Keys are stored (protected with security) in Fusion devices in nonvolatile flash memory. All programming files sent to the device can be authenticated by the part prior to programming to ensure that bad programming data is not loaded into the part that may possibly damage it. All programming verification is performed on-chip, ensuring that the contents of Fusion devices remain as secure as possible.

AES decryption can also be used on the 1,024-bit FlashROM to allow for remote updates of the FlashROM contents. This allows for easy support of subscription model products and protects them with measures designed to provide the highest level of security available. See the application note *Fusion Security* for more details.

AES for Flash Memory

AES decryption can also be used on the flash memory blocks. This provides the best available security during update of the flash memory blocks. During runtime, the encrypted data can be clocked in via the JTAG interface. The data can be passed through the internal AES decryption engine, and the decrypted data can then be stored in the flash memory block.

Programming

Programming can be performed using various programming tools, such as Silicon Sculptor II (BP Micro Systems) or FlashPro3 (Microsemi).

The user can generate STP programming files from the Designer software and can use these files to program a device.

Fusion devices can be programmed in-system. During programming, VCCOSC is needed in order to power the internal 100 MHz oscillator. This oscillator is used as a source for the 20 MHz oscillator that is used to drive the charge pump for programming.

Table 3-3 • **Input Resistance of Analog Pads**

Pads	Pad Configuration	Prescaler Range	Input Resistance to Ground
AV, AC	Analog Input (direct input to ADC)	–	2 kΩ (typical)
		–	> 10 MΩ
	Analog Input (positive prescaler)	+16 V to +2 V	1 MΩ (typical)
		+1 V to +0.125 V	> 10 MΩ
	Analog Input (negative prescaler)	–16 V to –2 V	1 MΩ (typical)
		–1 V to –0.125 V	> 10 MΩ
	Digital input	+16 V to +2 V	1 MΩ (typical)
	Current monitor	+16 V to +2 V	1 MΩ (typical)
		–16 V to –2 V	1 MΩ (typical)
AT	Analog Input (direct input to ADC)	–	1 MΩ (typical)
	Analog Input (positive prescaler)	+16 V, +4 V	1 MΩ (typical)
	Digital input	+16 V, +4 V	1 MΩ (typical)
	Temperature monitor	+16 V, +4 V	> 10 MΩ

Table 3-4 • **Overshoot and Undershoot Limits** [1]

VCCI	Average VCCI–GND Overshoot or Undershoot Duration as a Percentage of Clock Cycle[2]	Maximum Overshoot/ Undershoot[2]
2.7 V or less	10%	1.4 V
	5%	1.49 V
3.0 V	10%	1.1 V
	5%	1.19 V
3.3 V	10%	0.79 V
	5%	0.88 V
3.6 V	10%	0.45 V
	5%	0.54 V

Notes:

1. *Based on reliability requirements at a junction temperature of 85°C.*
2. *The duration is allowed at one cycle out of six clock cycle. If the overshoot/undershoot occurs at one out of two cycles, the maximum overshoot/undershoot has to be reduced by 0.15 V.*

Table 3-13 **• Summary of I/O Output Buffer Power (per pin)—Default I/O Software Settings[1]**

	C_{LOAD} (pF)	VCCI (V)	Static Power PDC8 (mW)[2]	Dynamic Power PAC10 (µW/MHz)[3]
Applicable to Pro I/O Banks				
Single-Ended				
3.3 V LVTTL/LVCMOS	35	3.3	–	474.70
2.5 V LVCMOS	35	2.5	–	270.73
1.8 V LVCMOS	35	1.8	–	151.78
1.5 V LVCMOS (JESD8-11)	35	1.5	–	104.55
3.3 V PCI	10	3.3	–	204.61
3.3 V PCI-X	10	3.3	–	204.61
Voltage-Referenced				
3.3 V GTL	10	3.3	–	24.08
2.5 V GTL	10	2.5	–	13.52
3.3 V GTL+	10	3.3	–	24.10
2.5 V GTL+	10	2.5	–	13.54
HSTL (I)	20	1.5	7.08	26.22
HSTL (II)	20	1.5	13.88	27.22
SSTL2 (I)	30	2.5	16.69	105.56
SSTL2 (II)	30	2.5	25.91	116.60
SSTL3 (I)	30	3.3	26.02	114.87
SSTL3 (II)	30	3.3	42.21	131.76
Differential				
LVDS	–	2.5	7.70	89.62
LVPECL	–	3.3	19.42	168.02
Applicable to Advanced I/O Banks				
Single-Ended				
3.3 V LVTTL / 3.3 V LVCMOS	35	3.3	–	468.67
2.5 V LVCMOS	35	2.5	–	267.48
1.8 V LVCMOS	35	1.8	–	149.46
1.5 V LVCMOS (JESD8-11)	35	1.5	–	103.12
3.3 V PCI	10	3.3	–	201.02
3.3 V PCI-X	10	3.3	–	201.02

Notes:

1. *Dynamic power consumption is given for standard load and software-default drive strength and output slew.*
2. *PDC8 is the static power (where applicable) measured on VCCI.*
3. *PAC10 is the total dynamic power measured on VCC and VCCI.*

$P_{S\text{-}CELL} = 0\ W$

$P_{C\text{-}CELL} = 0\ W$

$P_{NET} = 0\ W$

$P_{LOGIC} = 0\ W$

I/O Input and Output Buffer Contribution—$P_{I/O}$

This example uses LVTTL 3.3 V I/O cells. The output buffers are 12 mA–capable, configured with high output slew and driving a 35 pF output load.

$F_{CLK} = 50\ MHz$

Number of input pins used: $N_{INPUTS} = 30$

Number of output pins used: $N_{OUTPUTS} = 40$

Estimated I/O buffer toggle rate: $\alpha_2 = 0.1$ (10%)

Estimated IO buffer enable rate: $\beta_1 = 1$ (100%)

Operating Mode

$P_{INPUTS} = N_{INPUTS} * (\alpha_2 / 2) * PAC9 * F_{CLK}$

$P_{INPUTS} = 30 * (0.1 / 2) * 0.01739 * 50$

$P_{INPUTS} = 1.30\ mW$

$P_{OUTPUTS} = N_{OUTPUTS} * (\alpha_2 / 2) * \beta_1 * PAC10 * F_{CLK}$

$P_{OUTPUTS} = 40 * (0.1 / 2) * 1 * 0.4747 * 50$

$P_{OUTPUTS} = 47.47\ mW$

$P_{I/O} = P_{INPUTS} + P_{OUTPUTS}$

$P_{I/O} = 1.30\ mW + 47.47\ mW$

$P_{I/O} = 48.77\ mW$

Standby Mode and Sleep Mode

$P_{INPUTS} = 0\ W$

$P_{OUTPUTS} = 0\ W$

$P_{I/O} = 0\ W$

RAM Contribution—P_{MEMORY}

Frequency of Read Clock: $F_{READ\text{-}CLOCK} = 10\ MHz$

Frequency of Write Clock: $F_{WRITE\text{-}CLOCK} = 10\ MHz$

Number of RAM blocks: $N_{BLOCKS} = 20$

Estimated RAM Read Enable Rate: $\beta_2 = 0.125$ (12.5%)

Estimated RAM Write Enable Rate: $\beta_3 = 0.125$ (12.5%)

Operating Mode

$P_{MEMORY} = (N_{BLOCKS} * PAC11 * \beta_2 * F_{READ\text{-}CLOCK}) + (N_{BLOCKS} * PAC12 * \beta_3 * F_{WRITE\text{-}CLOCK})$

$P_{MEMORY} = (20 * 0.025 * 0.125 * 10) + (20 * 0.030 * 0.125 * 10)$

$P_{MEMORY} = 1.38\ mW$

Standby Mode and Sleep Mode

$P_{MEMORY} = 0\ W$

PQ208		
Pin Number	AFS250 Function	AFS600 Function
1	VCCPLA	VCCPLA
2	VCOMPLA	VCOMPLA
3	GNDQ	GAA2/IO85PDB4V0
4	VCCIB3	IO85NDB4V0
5	GAA2/IO76PDB3V0	GAB2/IO84PDB4V0
6	IO76NDB3V0	IO84NDB4V0
7	GAB2/IO75PDB3V0	GAC2/IO83PDB4V0
8	IO75NDB3V0	IO83NDB4V0
9	NC	IO77PDB4V0
10	NC	IO77NDB4V0
11	VCC	IO76PDB4V0
12	GND	IO76NDB4V0
13	VCCIB3	VCC
14	IO72PDB3V0	GND
15	IO72NDB3V0	VCCIB4
16	GFA2/IO71PDB3V0	GFA2/IO75PDB4V0
17	IO71NDB3V0	IO75NDB4V0
18	GFB2/IO70PDB3V0	GFC2/IO73PDB4V0
19	IO70NDB3V0	IO73NDB4V0
20	GFC2/IO69PDB3V0	VCCOSC
21	IO69NDB3V0	XTAL1
22	VCC	XTAL2
23	GND	GNDOSC
24	VCCIB3	GFC1/IO72PDB4V0
25	GFC1/IO68PDB3V0	GFC0/IO72NDB4V0
26	GFC0/IO68NDB3V0	GFB1/IO71PDB4V0
27	GFB1/IO67PDB3V0	GFB0/IO71NDB4V0
28	GFB0/IO67NDB3V0	GFA1/IO70PDB4V0
29	VCCOSC	GFA0/IO70NDB4V0
30	XTAL1	IO69PDB4V0
31	XTAL2	IO69NDB4V0
32	GNDOSC	VCC
33	GEB1/IO62PDB3V0	GND
34	GEB0/IO62NDB3V0	VCCIB4
35	GEA1/IO61PDB3V0	GEC1/IO63PDB4V0
36	GEA0/IO61NDB3V0	GEC0/IO63NDB4V0
37	GEC2/IO60PDB3V0	GEB1/IO62PDB4V0

PQ208		
Pin Number	AFS250 Function	AFS600 Function
38	IO60NDB3V0	GEB0/IO62NDB4V0
39	GND	GEA1/IO61PDB4V0
40	VCCIB3	GEA0/IO61NDB4V0
41	GEB2/IO59PDB3V0	GEC2/IO60PDB4V0
42	IO59NDB3V0	IO60NDB4V0
43	GEA2/IO58PDB3V0	VCCIB4
44	IO58NDB3V0	GNDQ
45	VCC	VCC
45	VCC	VCC
46	VCCNVM	VCCNVM
47	GNDNVM	GNDNVM
48	GND	GND
49	VCC15A	VCC15A
50	PCAP	PCAP
51	NCAP	NCAP
52	VCC33PMP	VCC33PMP
53	VCC33N	VCC33N
54	GNDA	GNDA
55	GNDAQ	GNDAQ
56	NC	AV0
57	NC	AC0
58	NC	AG0
59	NC	AT0
60	NC	ATRTN0
61	NC	AT1
62	NC	AG1
63	NC	AC1
64	NC	AV1
65	AV0	AV2
66	AC0	AC2
67	AG0	AG2
68	AT0	AT2
69	ATRTN0	ATRTN1
70	AT1	AT3
71	AG1	AG3
72	AC1	AC3
73	AV1	AV3

FG256				
Pin Number	**AFS090 Function**	**AFS250 Function**	**AFS600 Function**	**AFS1500 Function**
E13	VCCIB1	VCCIB1	VCCIB2	VCCIB2
E14	GCC2/IO33NDB1V0	IO42NDB1V0	IO32NDB2V0	IO46NDB2V0
E15	GCB2/IO33PDB1V0	GBC2/IO42PDB1V0	GBC2/IO32PDB2V0	GBC2/IO46PDB2V0
E16	GND	GND	GND	GND
F1	NC	NC	IO79NDB4V0	IO111NDB4V0
F2	NC	NC	IO79PDB4V0	IO111PDB4V0
F3	GFB1/IO48PPB3V0	IO72NDB3V0	IO76NDB4V0	IO112NDB4V0
F4	GFC0/IO49NDB3V0	IO72PDB3V0	IO76PDB4V0	IO112PDB4V0
F5	NC	NC	IO82PSB4V0	IO120PSB4V0
F6	GFC1/IO49PDB3V0	GAC2/IO74PPB3V0	GAC2/IO83PPB4V0	GAC2/IO123PPB4V0
F7	NC	IO09RSB0V0	IO04PPB0V0	IO05PPB0V1
F8	NC	IO19RSB0V0	IO08NDB0V1	IO11NDB0V1
F9	NC	NC	IO20PDB1V0	IO27PDB1V1
F10	NC	IO29RSB0V0	IO23NDB1V1	IO37NDB1V2
F11	NC	IO43NDB1V0	IO36NDB2V0	IO50NDB2V0
F12	NC	IO43PDB1V0	IO36PDB2V0	IO50PDB2V0
F13	NC	IO44NDB1V0	IO39NDB2V0	IO59NDB2V0
F14	NC	GCA2/IO44PDB1V0	GCA2/IO39PDB2V0	GCA2/IO59PDB2V0
F15	GCC1/IO34PDB1V0	GCB2/IO45PDB1V0	GCB2/IO40PDB2V0	GCB2/IO60PDB2V0
F16	GCC0/IO34NDB1V0	IO45NDB1V0	IO40NDB2V0	IO60NDB2V0
G1	GEC0/IO46NPB3V0	IO70NPB3V0	IO74NPB4V0	IO109NPB4V0
G2	VCCIB3	VCCIB3	VCCIB4	VCCIB4
G3	GEC1/IO46PPB3V0	GFB2/IO70PPB3V0	GFB2/IO74PPB4V0	GFB2/IO109PPB4V0
G4	GFA1/IO47PDB3V0	GFA2/IO71PDB3V0	GFA2/IO75PDB4V0	GFA2/IO110PDB4V0
G5	GND	GND	GND	GND
G6	GFA0/IO47NDB3V0	IO71NDB3V0	IO75NDB4V0	IO110NDB4V0
G7	GND	GND	GND	GND
G8	VCC	VCC	VCC	VCC
G9	GND	GND	GND	GND
G10	VCC	VCC	VCC	VCC
G11	GDA1/IO37NDB1V0	GCC0/IO47NDB1V0	GCC0/IO43NDB2V0	GCC0/IO62NDB2V0
G12	GND	GND	GND	GND
G13	IO37PDB1V0	GCC1/IO47PDB1V0	GCC1/IO43PDB2V0	GCC1/IO62PDB2V0
G14	GCB0/IO35NPB1V0	IO46NPB1V0	IO41NPB2V0	IO61NPB2V0
G15	VCCIB1	VCCIB1	VCCIB2	VCCIB2
G16	GCB1/IO35PPB1V0	GCC2/IO46PPB1V0	GCC2/IO41PPB2V0	GCC2/IO61PPB2V0
H1	GEB1/IO45PDB3V0	GFC2/IO69PDB3V0	GFC2/IO73PDB4V0	GFC2/IO108PDB4V0
H2	GEB0/IO45NDB3V0	IO69NDB3V0	IO73NDB4V0	IO108NDB4V0

Revision	Changes	Page
Revision 2 (continued)	A note was added to Figure 2-27 • Real-Time Counter System (not all the signals are shown for the AB macro) stating that the user is only required to instantiate the VRPSM macro if the user wishes to specify PUPO behavior of the voltage regulator to be different from the default, or employ user logic to shut the voltage regulator off (SAR 21773).	2-31
	VPUMP was incorrectly represented as VPP in several places. This was corrected to VPUMP in the "Standby and Sleep Mode Circuit Implementation" section and Table 3-8 • AFS1500 Quiescent Supply Current Characteristics through Table 3-11 • AFS090 Quiescent Supply Current Characteristics (21963).	2-32, 3-10
	Additional information was added to the Flash Memory Block "Write Operation" section, including an explanation of the fact that a copy-page operation takes no less than 55 cycles (SAR 26338).	2-45
	The "FlashROM" section was revised to refer to Figure 2-46 • FlashROM Timing Diagram and Table 2-26 • FlashROM Access Time rather than stating 20 MHz as the maximum FlashROM access clock and 10 ns as the time interval for D0 to become valid or invalid (SAR 22105).	2-53, 2-54
	The following figures were deleted (SAR 29991). Reference was made to a new application note, *Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs,* which covers these cases in detail (SAR 34862). Figure 2-55 • Write Access after Write onto Same Address Figure 2-56 • Read Access after Write onto Same Address Figure 2-57 • Write Access after Read onto Same Address	
	The port names in the SRAM "Timing Waveforms", "Timing Characteristics", SRAM tables, Figure 2-55 • RAM Reset. Applicable to both RAM4K9 and RAM512x18., and the FIFO "Timing Characteristics" tables were revised to ensure consistency with the software names (SAR 35753).	2-63, 2-66, 2-65, 2-75
	In several places throughout the datasheet, GNDREF was corrected to ADCGNDREF (SAR 20783): Figure 2-64 • Analog Block Macro Table 2-36 • Analog Block Pin Description "ADC Operation" section	 2-77 2-78 2-104
	The following note was added below Figure 2-78 • Timing Diagram for the Temperature Monitor Strobe Signal: When the IEEE 1149.1 Boundary Scan EXTEST instruction is executed, the AG pad drive strength ceases and becomes a 1 µA sink into the Fusion device. (SAR 24796).	2-93
	The "Analog-to-Digital Converter Block" section was extensively revised, reorganizing the information and adding the "ADC Theory of Operation" section and "Acquisition Time or Sample Time Control" section. The "ADC Example" section was reworked and corrected (SAR 20577).	2-96
	Table 2-49 • Analog Channel Specifications was modified to include calibrated and uncalibrated values for offset (AFS090 and AFS250) for the external and internal temperature monitors. The "Offset" section was revised accordingly and now references Table 2-49 • Analog Channel Specifications (SARs 22647, 27015).	2-95, 2-117
	The "Intra-Conversion" section and "Injected Conversion" section had definitions incorrectly interchanged and have been corrected. Figure 2-92 • Intra-Conversion Timing Diagram and Figure 2-93 • Injected Conversion Timing Diagram were also incorrectly interchanged and have been replaced correctly. Reference in the figure notes to EQ 10 has been corrected to EQ 23 (SAR 20547).	2-110, 2-113, 2-113

Revision	Changes	Page
Advance v1.0 (January 2008)	All Timing Characteristics tables were updated. For the Differential I/O Standards, the Standard I/O support tables are new.	N/A
	Table 2-3 • Array Coordinates was updated to change the max x and y values	2-9
	Table 2-12 • Fusion CCC/PLL Specification was updated.	2-31
	A note was added to Table 2-16 · RTC ACM Memory Map.	2-37
	A reference to the Peripheral's User's Guide was added to the "Voltage Regulator Power Supply Monitor (VRPSM)" section.	2-42
	In Table 2-25 • Flash Memory Block Timing, the commercial conditions were updated.	2-55
	In Table 2-26 • FlashROM Access Time, the commercial conditions were missing and have been added below the title of the table.	2-58
	In Table 2-36 • Analog Block Pin Description, the function description was updated for the ADCRESET.	2-82
	In the "Voltage Monitor" section, the following sentence originally had ± 10% and it was changed to +10%. The Analog Quad inputs are tolerant up to 12 V + 10%. In addition, this statement was deleted from the datasheet: Each I/O will draw power when connected to power (3 mA at 3 V).	2-86
	The "Terminology" section is new.	2-88
	The "Current Monitor" section was significantly updated. Figure 2-72 • Timing Diagram for Current Monitor Strobe to Figure 2-74 • Negative Current Monitor and Table 2-37 • Recommended Resistor for Different Current Range Measurement are new.	2-90
	The "ADC Description" section was updated to add the "Terminology" section.	2-93
	In the "Gate Driver" section, 25 mA was changed to 20 mA and 1.5 MHz was changed to 1.3 MHz. In addition, the following sentence was deleted: The maximum AG pad switching frequency is 1.25 MHz.	2-94
	The "Temperature Monitor" section was updated to rewrite most of the text and add Figure 2-78, Figure 2-79, and Table 2-38 • Temperature Data Format.	2-96
	In Table 2-38 • Temperature Data Format, the temperature K column was changed for 85°C from 538 to 358.	2-98
	In Table 2-45 • ADC Interface Timing, "Typical-Case" was changed to "Worst-Case."	2-110
	The "ADC Interface Timing" section is new.	2-110
	Table 2-46 • Analog Channel Specifications was updated.	2-118
	The "V_{CC15A} Analog Power Supply (1.5 V)" section was updated.	2-224
	The "$V_{CCPLA/B}$ PLL Supply Voltage" section is new.	2-225
	In "V_{CCNVM} Flash Memory Block Power Supply (1.5 V)" section, supply was changed to supply input.	2-224
	The "$V_{CCPLA/B}$ PLL Supply Voltage" pin description was updated to include the following statement: Actel recommends tying VCCPLX to VCC and using proper filtering circuits to decouple V_{CC} noise from PLL.	2-225
	The "$V_{COMPLA/B}$ Ground for West and East PLL" section was updated.	2-225